



Docket No.: MUH-12041

10-29-02  
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BT  
Jan 2185  
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By: H. P. H.

Date: October 4, 2002

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Heinz Höngschmid  
Applic. No. : 09/997,983  
Filed : November 29, 2001  
Title : Integrated Magnetoresistive Semiconductor Memory and Fabrication Method for the Memory  
Art Unit : 2185

INFORMATION DISCLOSURE STATEMENT

Hon. Commissioner of Patents and Trademarks,  
Washington, D.C. 20231

Sir:

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Technology Center 2100

In accordance with 37 C.F.R. 1.98 copies of the following patents and/or publications are submitted herewith:

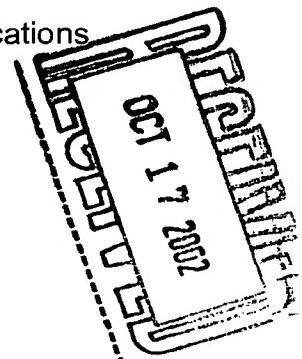
United States Patent No. 5,940,319 (Durlam et al.), dated August 17, 1999;

United States Patent No. 6,097,625 (Scheuerlein), dated August 1, 2000;

M. Durlam et al.: "Nonvolatile RAM based on Magnetic Tunnel Junction Elements", *2000 IEEE International Solid-State Circuits Conference, Digest of Technical Papers*, pp. 130-131;

S. Tehrani et al.: "Recent Developments in Magnetic Tunnel Junction MRAM", *IEEE Transactions on Magnetics*, Vol. 36, No. 5, September 2000, pp. 2752-2757;

German Examination Report dated November 14, 2001.



If no translation of pertinent portions of any foreign language patents or publications mentioned above is included with the aforementioned copies of those applications, patents and/or publications, it is because no existing translation is readily available to the applicant.

Respectfully submitted,



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For Applicant

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Date: October 4, 2002

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